

# MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV

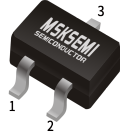
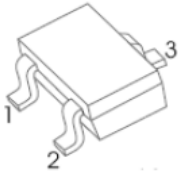


GDT



PLED

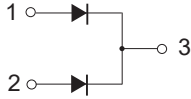
Product data sheet



## BAV70W SWITCHING DIODE

### FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



**SOT-323**

**MARKING: KJA**

### Maximum Ratings @Ta=25°C

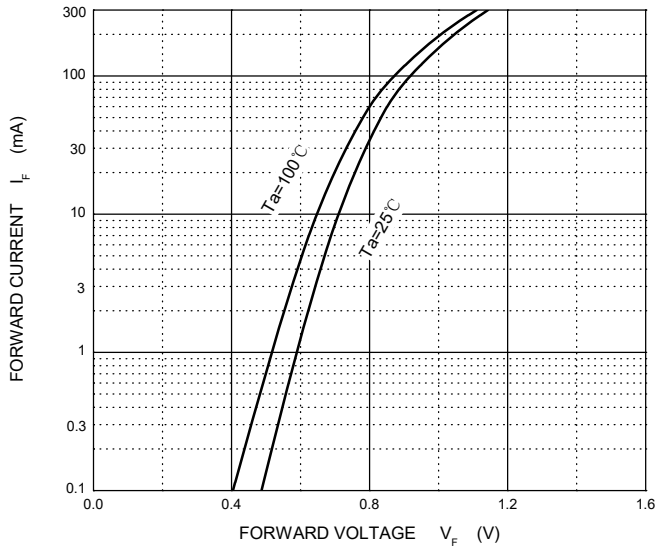
| Parameter   | Symbol          | Limit    | Unit |
|---|-----------------|----------|------|
| Non-Repetitive Peak Reverse Voltage                   | $V_{RM}$        | 100      | V    |
| Peak Repetitive Peak Reverse Voltage                  | $V_{RRM}$       | 75       | V    |
| Working Peak Reverse Voltage                          | $V_{RWM}$       |          |      |
| DC Blocking Voltage                                   | $V_R$           |          |      |
| RMS Reverse Voltage                                   | $V_{R(RMS)}$    | 53       | V    |
| Forward Continuous Current                            | $I_{FM}$        | 300      | mA   |
| Average Rectified Output Current                      | $I_O$           | 150      | mA   |
| Non-Repetitive Peak Forward Surge Current<br>@t=8.3ms | $I_{FSM}$       | 2.0      | A    |
| Power Dissipation                                     | $P_d$           | 200      | mW   |
| Thermal Resistance Junction to Ambient                | $R_{\theta JA}$ | 625      | °C/W |
| Junction Temperature                                  | $T_j$           | 150      | °C   |
| Storage Temperature                                   | $T_{STG}$       | -55~+150 | °C   |

### Electrical Ratings @Ta=25°C

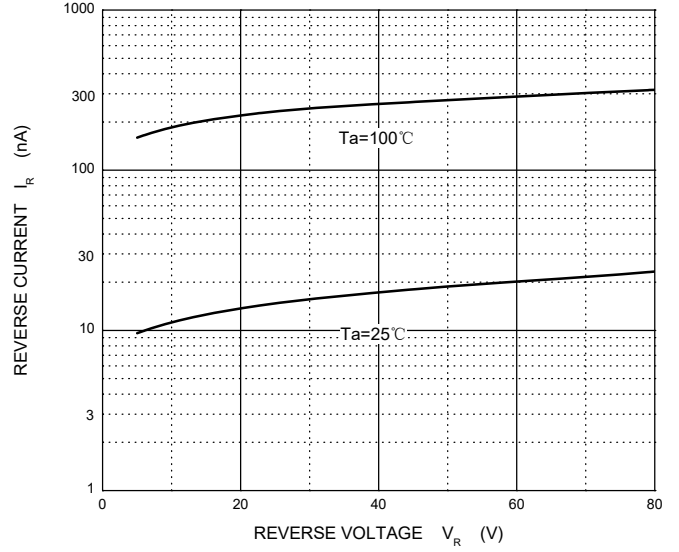
| Parameter                     | Symbol     | Min | Typ | Max   | Unit    | Conditions                                       |
|-------------------------------|------------|-----|-----|-------|---------|--|
| Reverse breakdown voltage     | $V_{(BR)}$ | 75  |     |       | V       | $I_R=100\mu A$                                   |
| Forward voltage               | $V_{F1}$   |     |     | 0.715 | V       | $I_F=1mA$  |
|                               | $V_{F2}$   |     |     | 0.855 | V       | $I_F=10mA$                                       |
|                               | $V_{F3}$   |     |     | 1.0   | V       | $I_F=50mA$                                       |
|                               | $V_{F4}$   |     |     | 1.25  | V       | $I_F=150mA$                                      |
| Reverse current               | $I_{R1}$   |     |     | 2.5   | $\mu A$ | $V_R=75V$  |
|                               | $I_{R2}$   |     |     | 25    | nA      | $V_R=20V$  |
| Capacitance between terminals | $C_T$      |     |     | 2     | pF      | $V_R=0V, f=1MHz$                                 |
| Reverse recovery time         | $t_{rr}$   |     |     | 4     | ns      | $I_F=I_R=10mA$<br>$I_{rr}=0.1I_R, R_L=100\Omega$ |

**Typical Characteristics**

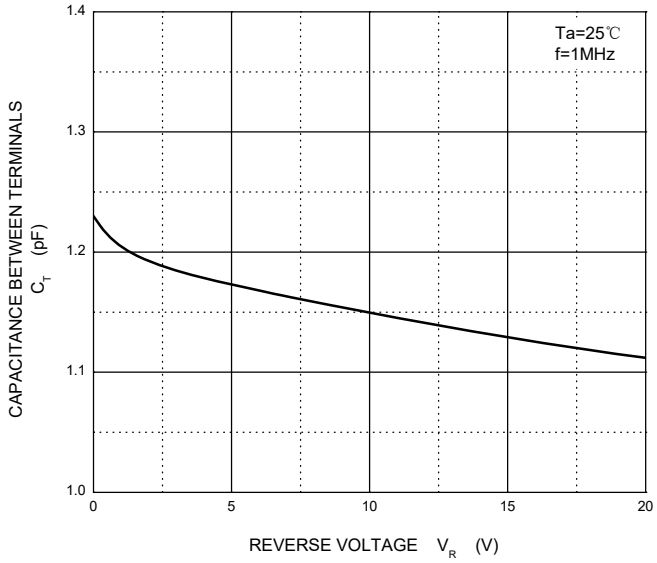
**Forward Characteristics**



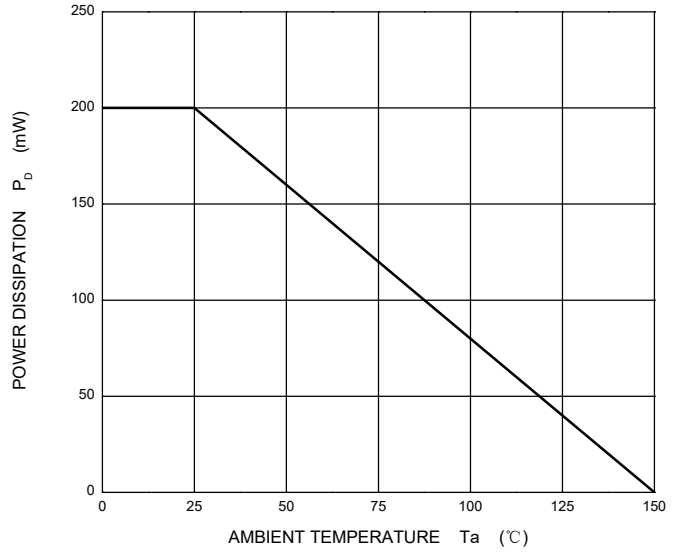
**Reverse Characteristics**



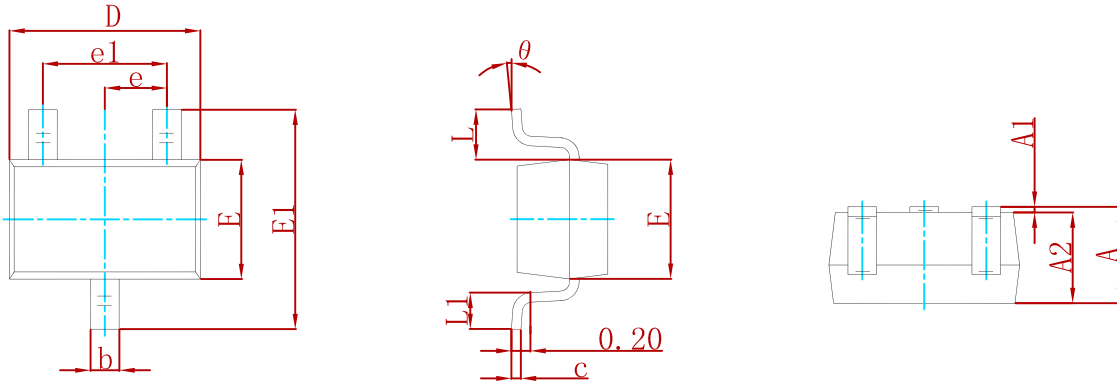
**Capacitance Characteristics**



**Power Derating Curve**

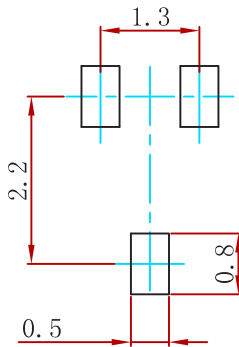


**PACKAGE MECHANICAL DATA**



| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min                       | Max   | Min                  | Max   |
| A      | 0.900                     | 1.100 | 0.035                | 0.043 |
| A1     | 0.000                     | 0.100 | 0.000                | 0.004 |
| A2     | 0.900                     | 1.000 | 0.035                | 0.039 |
| b      | 0.200                     | 0.400 | 0.008                | 0.016 |
| c      | 0.080                     | 0.150 | 0.003                | 0.006 |
| D      | 2.000                     | 2.200 | 0.079                | 0.087 |
| E      | 1.150                     | 1.350 | 0.045                | 0.053 |
| E1     | 2.150                     | 2.450 | 0.085                | 0.096 |
| e      | 0.650 TYP                 |       | 0.026 TYP            |       |
| e1     | 1.200                     | 1.400 | 0.047                | 0.055 |
| L      | 0.525 REF                 |       | 0.021 REF            |       |
| L1     | 0.260                     | 0.460 | 0.010                | 0.018 |
| θ      | 0°                        | 8°    | 0°                   | 8°    |

**Suggested Pad Layout**



Note:  
 1. Controlling dimension: in millimeters.  
 2. General tolerance: ±0.05mm.  
 3. The pad layout is for reference purposes only.

**REEL SPECIFICATION**

| P/N    | PKG     | QTY  |
|--------|---------|------|
| BAV70W | SOT-323 | 3000 |

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